

No.2162A

2SA1522/2SC3916

PNP/ NPN Epitaxial Planar Silicon Transistors

Switching Applications (with Bias Resistance)

Applications

. Switching circuits, inverter circuits, interface circuits, driver circuits

Features

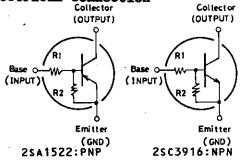
- . On-chip bias resistance $(R_1\!=\!10\mathrm{k}\Omega,\,R_2\!=\!10\mathrm{k}\Omega)$
- . Small-sized package (SPA)
- Large current capacity (I_C=500mA)

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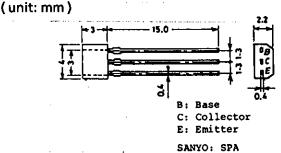
Absolute Maximum Ratings at Ta=	25 ⁰ C		unit
Collector to Base Voltage	v _{CBO}	(-)50	V
Collector to Emitter Voltage	V _{CEO}	(-)50	v
Emitter to Base Voltage	V _{EBO}	(-)10	V
Collector Current	IC	(-)500	mA
Collector Current (Pulse)	I _{CP}	(-)800	mA
Collector Dissipation		300	mW
Junction Temperature	PC Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

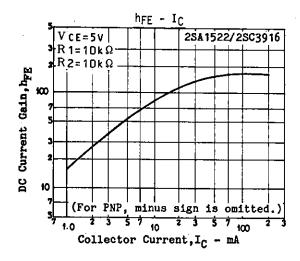
Electrical Characteristics	at Ta=25 ⁰ C	min	typ	max unit
Collector Cutoff Current	I_{CBO} $V_{CB}=(-)40V, I_{E}=0$		(-	-)0.1 μA
	I_{CEO} $V_{CE}=(-)40V, I_{B}=0$		-	-)0.5 μA
Emitter Cutoff Current	I_{EBO} $V_{\text{EB}}=(-)5V, I_{\text{C}}=0$	(-)195	(-)250 (-	-)360 μA
DC Current Gain	$h_{FE} = V_{CE} = (-)5V, I_{C} = (-)10mA$	50		•
Gain-Bandwidth Product	$f_{\rm T}^{-}$ $V_{\rm CE}^{-}=(-)10V, I_{\rm C}=(-)5mA$		250	MHz
1	1 02 0	:	(200)	MHz
Output Capacitance	$c_{ob} V_{CB} = (-)10V, f = 1MHz$,	3.7	pF
•	`	1	(5.5)	pF
C-E Saturation Voltage	$V_{CE(sat)}$ $I_{C}=(-)20mA$, $I_{B}=(-)1mA$:	(-)0.1 (-	-)0.3 V
C-B Breakdown Voltage	$V_{(BR)CBO} I_{C} = (-)10\mu A, I_{E} = 0$	(-)50		v
C⊢E Breakdown Voltage	$V(BR)CEO$ $I_C=(-)100\mu A, R_{BE}=\infty$	(-)50		v
Input OFF-State Voltage	$V_{T(Off)} V_{CE} = (-)5V, I_{C} = (-)100\mu A$	(-)0.8	(-)1.1 (-	-)1.5 V
Input ON-State Voltage	$V_{\rm I(on)}^{\rm I(on)}$ $V_{\rm CE}^{\rm II}=(-)0.2V, I_{\rm C}=(-)10m$	A(-)1.0	(-)2.0 (-	-)4.0 V
Input Resistance	R ₁	7	10	13 kΩ
Resistance Ratio	R ₁ /R ₂	0.9	1.0	1.1

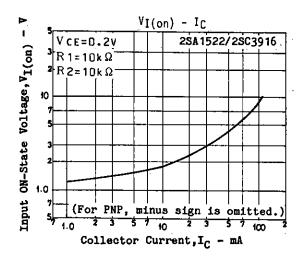
Electrical Connection

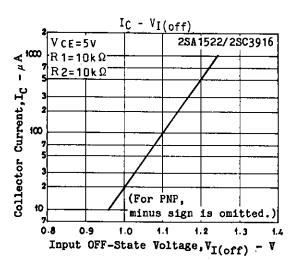


Package Dimensions 2033









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